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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 10

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Application Number	Not Yet Assigned
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First Named Inventor	John Moore
Art Unit	N/A
Examiner Name	Not Yet Assigned
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Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Sheet 2 of 10

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First Named Inventor	John Moore
Art Unit	N/A
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Sheet	3	of	10

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* GJ	BA	WO 02/21542	03/14/2002	Kozicki et al.		
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Examiner Signature		Date Considered	11/29/04

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Sheet 4 | 10

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First Named Inventor	John Moore
Group Art Unit	N/A
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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First Named Inventor	John Moore
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Sheet 6 | 10

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First Named Inventor	John Moore
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Application Number	Not Yet Assigned
Filing Date	October 8, 2003
First Named Inventor	John Moore
Group Art Unit	N/A
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Attorney Docket Number	M4065.0488/P488-A

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Sheet 9 | 10

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First Named Inventor	John Moore
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*	CD6	PCT Written Opinion dated 8/20/03.	

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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
**	A	US 2004/0035401	2/2004	Ramachandran et al.	
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**		V2	US 6,514,805	2/2003	Xu et al.	
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**		X2	US 6,534,781	3/2003	Dennison	
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**		Z2	US 6,545,907	4/2003	Lowery et al.	
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Sheet 3 of 3

Complete if Known	
Application Number	10/680,161
Filing Date	October 8, 2003
First Named Inventor	John Moore et al.
Art Unit	2818
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0488/P488-A

** GD		R3	US 6,646,297	11/2003	Dennison	
**		S3	US 6,649,928	11/2003	Dennison	
**		T3	US 6,667,900	12/2003	Lowery et al.	
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Sheet 1 of 2

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Application Number	10/680,161
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Art Unit	N/A
Examiner Name	Not Yet Assigned
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CM					

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Examiner Signature		Date Considered	11/29/04

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Sheet 2 of 2

Complete if Known	
Application Number	10/680,161
Filing Date	October 8, 2003
First Named Inventor	John Moore
Art Unit	N/A
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0488/P488-A

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